

NTTFS4928NTAG-VB Datasheet

N-Channel 30 V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---------------------|----------------------------------|--------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) Typ. | I _D (A) | Q _g (Typ.) |
| 30 | 0.004 at V _{GS} = 4.5 V | 60 | 33.5 nC |
| | 0.005 at V _{GS} = 2.5 V | 50 | |

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

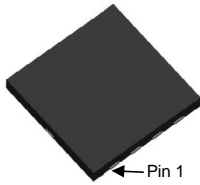


APPLICATIONS

- Motor Control
- Industrial
- Load Switch
- ORing

DFN 3x3 EP

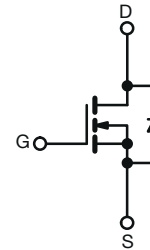
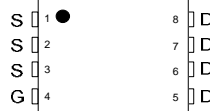
Top View



Bottom View



Top View



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | |
|---|-----------------------------------|------------------------|---------------------|---|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V _{DS} | 30 | V | |
| Gate-Source Voltage | V _{GS} | ± 20 | | |
| Continuous Drain Current (T _J = 150 °C) | I _D | T _C = 25 °C | 60 ^{a, e} | A |
| | | T _C = 70 °C | 40 ^{a, e} | |
| | | T _A = 25 °C | 22 ^{b, c} | |
| | | T _A = 70 °C | 15 ^{b, c} | |
| Pulsed Drain Current (t = 300 μs) | I _{DM} | 150 | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | 35 | |
| | | T _A = 25 °C | 3.3 ^{b, c} | |
| Single Pulse Avalanche Current | I _{AS} | 20 | | |
| Single Pulse Avalanche Energy | E _{AS} | 20 | mJ | |
| Maximum Power Dissipation | P _D | T _C = 25 °C | 52 | W |
| | | T _C = 70 °C | 33 | |
| | | T _A = 25 °C | 3.7 ^{b, c} | |
| | | T _A = 70 °C | 2.4 ^{b, c} | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C | |
| Soldering Recommendations (Peak Temperature) | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|-------------------|---------|---------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^{b, d} | R _{thJA} | 24 | 33 | °C/W | |
| Maximum Junction-to-Case (Drain) | R _{thJC} | 1.9 | 2.4 | | |

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 90 °C/W.
- Calculated based on maximum junction temperature. Package limitation current is 80 A.

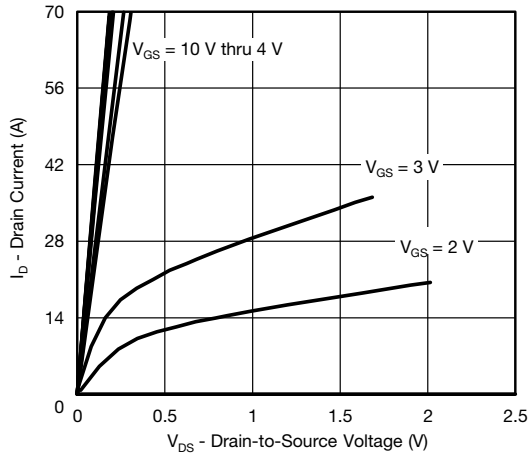
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|-------------------------|---|-------|--------|-----------|----------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 30 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | | 30 | | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | - 5.6 | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 0.5 | | 1.5 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 30 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$ | | 0.0040 | | Ω |
| | | $V_{GS} = 2.5\text{ V}, I_D = 7\text{ A}$ | | 0.0050 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 10\text{ A}$ | | 65 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 6000 | | pF |
| Output Capacitance | C_{oss} | | 406 | | | |
| Reverse Transfer Capacitance | C_{rss} | | 360 | | | |
| Total Gate Charge | Q_g | $V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ | | 68 | 102 | nC |
| | | $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$ | | 33.5 | 51 | |
| Gate-Source Charge | Q_{gs} | | 7.7 | | | |
| Gate-Drain Charge | Q_{gd} | | 13.8 | | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | 0.3 | 0.7 | 1.4 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$ | | 24 | 45 | ns |
| Rise Time | t_r | | 24 | 45 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | 32 | 60 | | |
| Fall Time | t_f | | 12 | 24 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | 14 | 28 | |
| Rise Time | t_r | | 13 | 26 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | 33 | 60 | | |
| Fall Time | t_f | | 8 | 16 | | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | | 35 | | A |
| Pulse Diode Forward Current | I_{SM} | | | 70 | | |
| Body Diode Voltage | V_{SD} | $I_S = 3\text{ A}, V_{GS} = 0\text{ V}$ | | 0.7 | 1.1 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 10\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | | 21 | 40 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | 10 | 20 | nC | |
| Reverse Recovery Fall Time | t_a | | 9 | | ns | |
| Reverse Recovery Rise Time | t_b | | 12 | | | |

Notes:

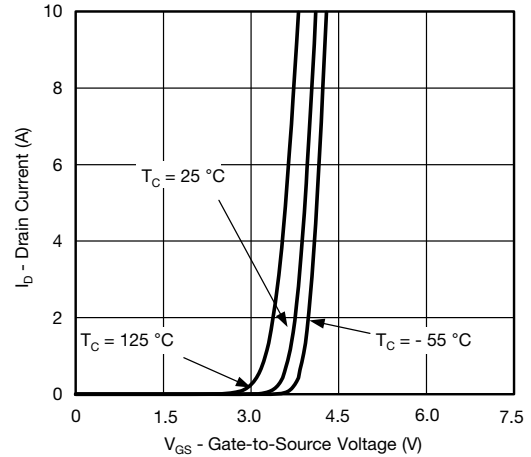
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

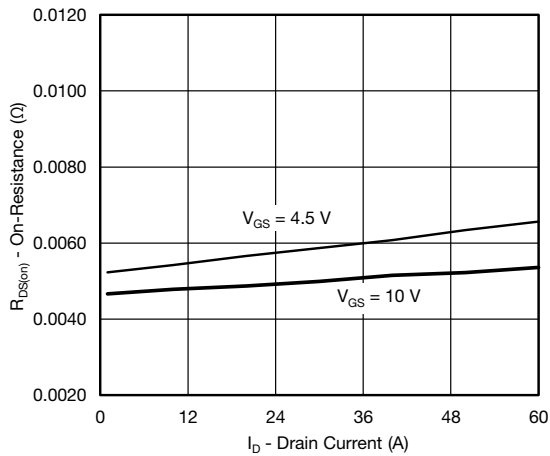
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



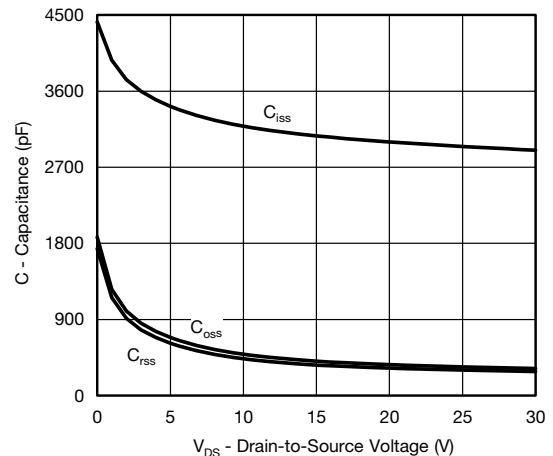
Output Characteristics



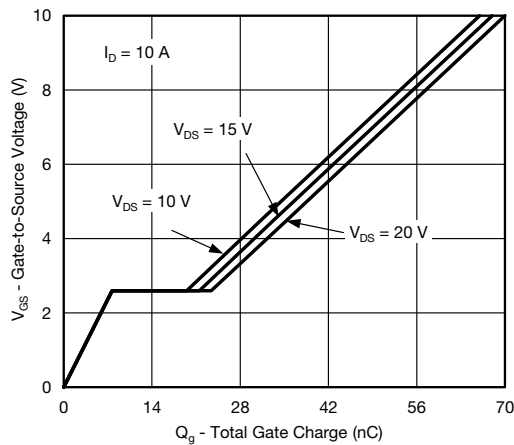
Transfer Characteristics



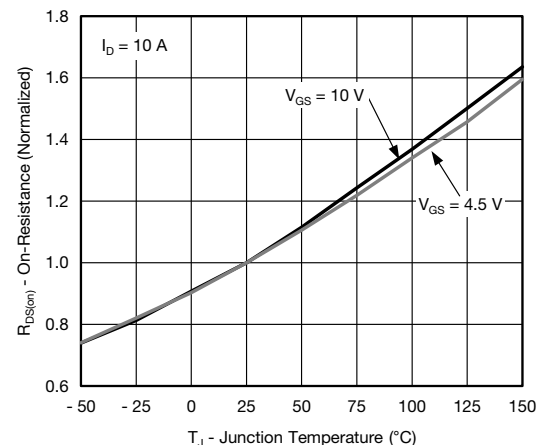
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

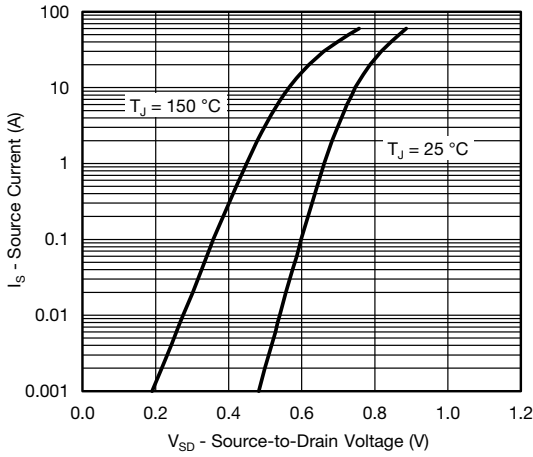


Gate Charge

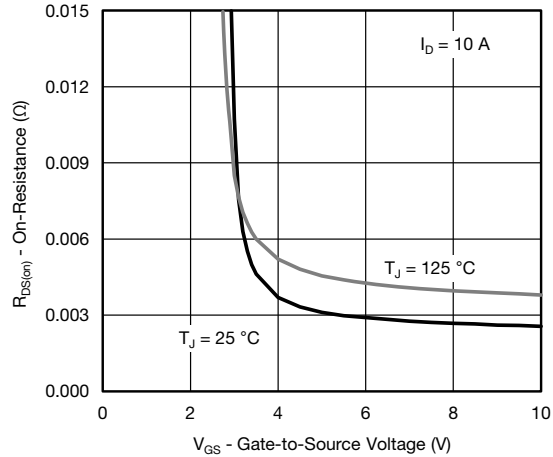


On-Resistance vs. Junction Temperature

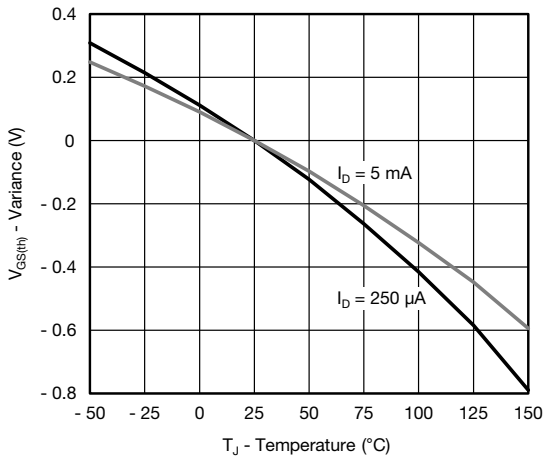
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



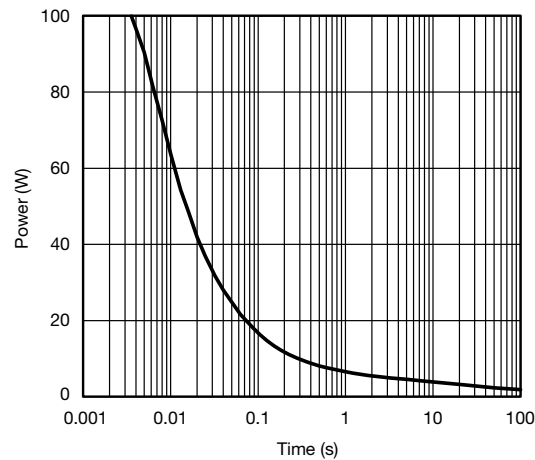
Source-Drain Diode Forward Voltage



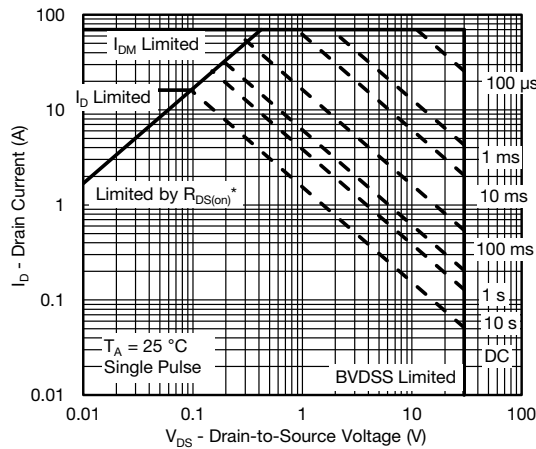
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



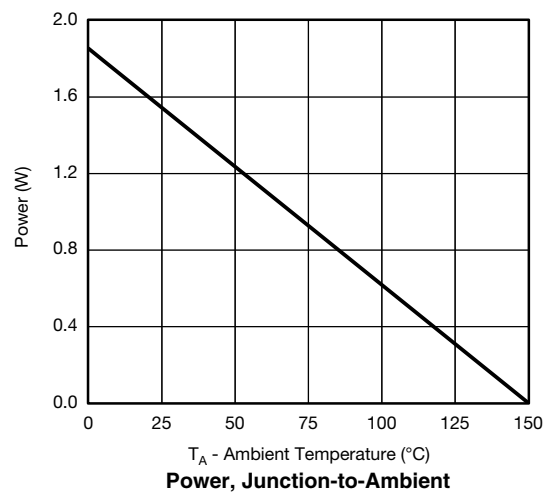
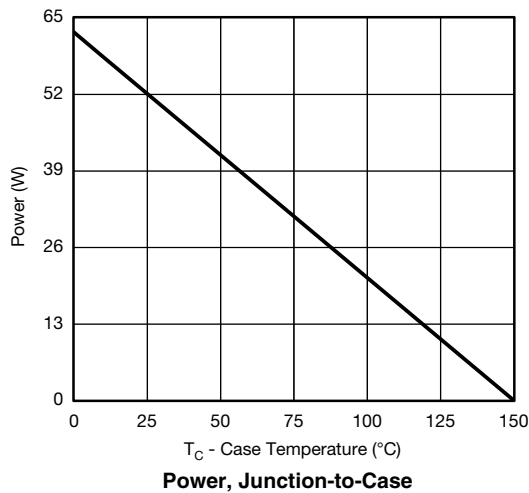
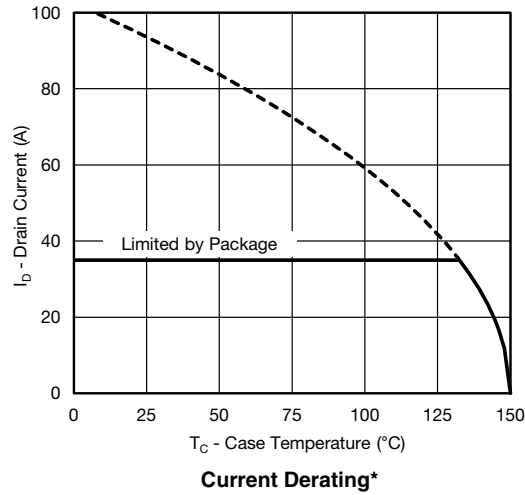
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

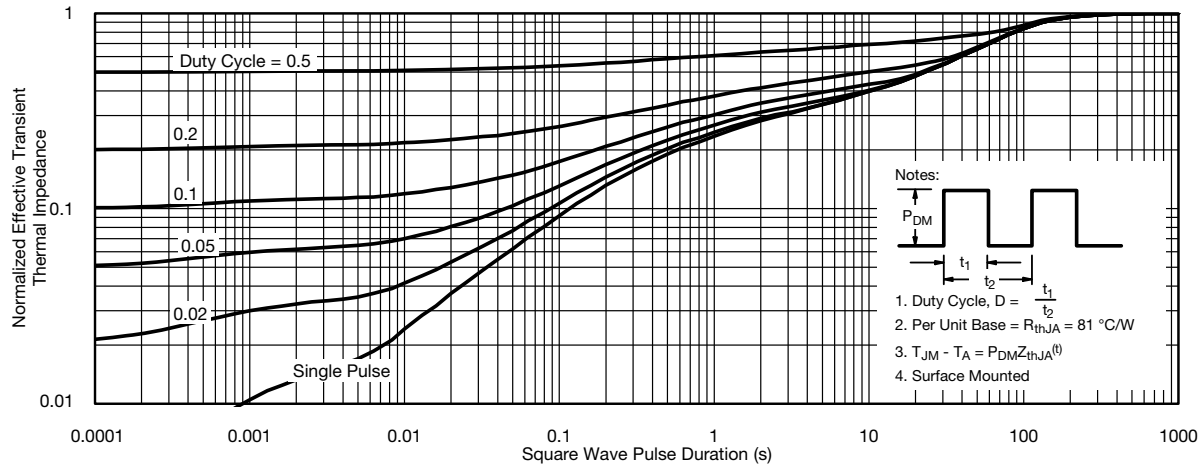
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

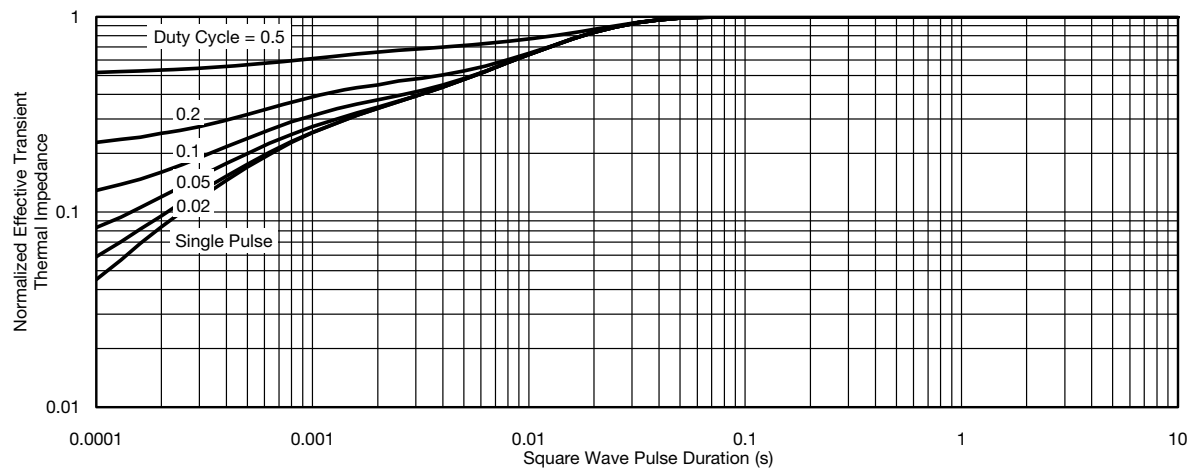


* The power dissipation P_D is based on T_{J(max.)} = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

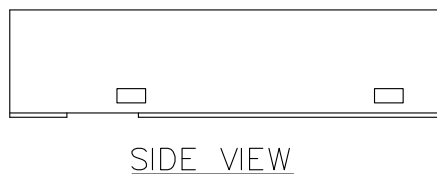
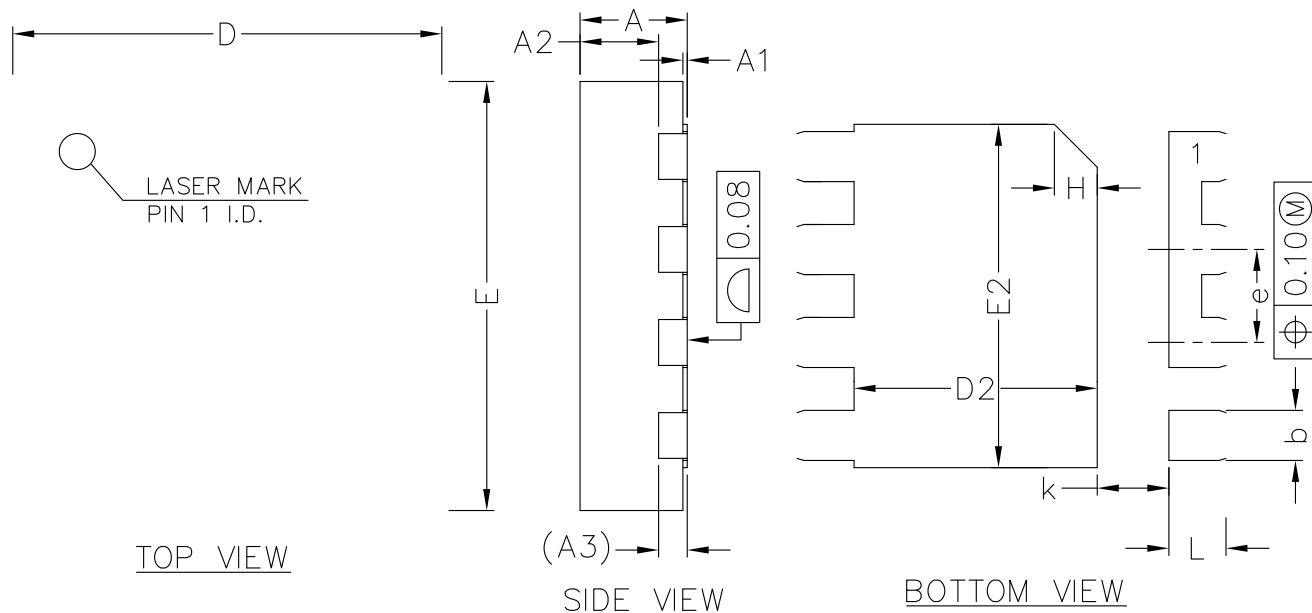
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

| SYMBOL | MIN | NOM | MAX |
|--------|---------|------|------|
| A | 0.70 | 0.75 | 0.80 |
| A1 | 0.00 | 0.02 | 0.05 |
| A2 | 0.50 | 0.55 | 0.60 |
| A3 | 0.20REF | | |
| b | 0.30 | 0.35 | 0.40 |
| D | 2.90 | 3.00 | 3.10 |
| E | 2.90 | 3.00 | 3.10 |
| D2 | 1.60 | 1.70 | 1.80 |
| E2 | 2.30 | 2.40 | 2.50 |
| e | 0.55 | 0.65 | 0.75 |
| K | 0.40 | 0.50 | 0.60 |
| L | 0.35 | 0.40 | 0.45 |

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